

ATOMIC LAYER DEPOSITION

What We Offer

Design &
Simulation



Prototyping &
Fabrication



Testing &
Characterization



Atomic layer deposition (ALD) is a thin-film deposition technique that builds materials one atomic layer at a time through sequential, self-limiting surface reactions. This precise process enables uniform coatings on complex surfaces and supports key advances in electronics, energy technologies, and advanced materials.

Key applications

**Advanced semiconductor
manufacturing and
microelectronics**

**Optics and protective
coatings for precision
components**

**Coatings for high-
aspect-ratio
structures**

**Surface passivation
and barrier layers**

- **Fiji F200 Cambridge NanoTech**
- Gases: argon as a carrier gas, oxygen and nitrogen for plasma assisted modes
- Deposition temperature up to 350 °C
- Precursor temperature up to 200 °C
- Wafer size up to 8" and up to 6.35mm height
- Materials: Al_2O_3 , TiO_2 , HfO_2 , Nb_2O_5

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- **SAVANNAH 200 Veeco Instruments**
- Metal oxide coatings such as SiO_2 , HfO_2 , TiO_2 , etc
- Physical thickness of coatings from a few nm to a few μm

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Features

- Single layer and multilayer coatings
- Flexible deposition modes including continuous high-speed deposition, exposure mode for complex high-aspect-ratio structures, and plasma-assisted deposition



If you have any questions, please contact us by email: info@chips2.lt



Funded by
the European Union
NextGenerationEU